

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				ATTY DOCKET NO. FIS9-2001-029 SUS3		SERIAL NO. 100-807629 10/047,964	
				Tze-Chiang Chen et al.			
				FILING 3/23/04 01/15/2002		GROUP 2925	

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						YES	NO
CL	WO 00/19523	06/06/2000	CA,CN,JP, European Patent				
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
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ATTY DOCKET NO.
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Tze-Chiang Chen et al.

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01/13/2002

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